

Please type a plus sign (+) inside this box → (+)

PTO/SB/08A (08-00)

Approved for use through 10/31/2002, OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
Application Number		Based on SN 10/035,441			
Filing Date		Filed: January 4, 2002			
First Named Inventor		Naoaki YAMAGUCHI et al.			
Group Art Unit		1765			
Examiner Name		Anita Karen Alanko			
Attorney Docket Number		0756-7191			
Sheet	3	of	3		

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
CL		5,472,505		Lee et al.	12/05/1995	_____
CL		5,294,518		Brady et al.	03/15/1994	_____
CL		5,240,581		Kim	08/31/1993	_____

FOREIGN PATENT DOCUMENTS							
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Office <sup>2</sup>	Number <sup>2</sup>	Kind Code <sup>2</sup> (if known)			

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
CL		G. Liu, S.J. Fonash, "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low Temperature Processing," Appl. Phys. Lett 62 (20), May 17, 1993, 1993 American Institute of Physics, pp. 2554-2556.	
CL		G. Liu and S.J. Fonash, "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing," Appl. Phys. Lett 55 (7), August 14, 1989, American Institute of Physics, pp. 660-662	
CL		R. Kakkad, G. Liu, S.J. Fonash, "Low Temperature Selective Crystallization of Amorphous Silicon," Journal of Non-Crystalline Solids, Volume 115, (1989), pp. 66-68.	

Examiner Signature	<i>calombie</i>	Date Considered	6.30.05
--------------------	-----------------	-----------------	---------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

BEST AVAILABLE COPY

Please type a plus sign (+) inside this box → (+)

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		<b>Complete If Known</b>	
Application Number		Based on SN 10/035,441	
Filing Date		Filed: January 4, 2002	
First Named Inventor		Naoaki YAMAGUCHI et al.	
Group Art Unit		1765	
Examiner Name		Anita Karen Alanko	
Attorney Docket Number		0756-7191	
Sheet	1	of	3

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
CL		5,808,318		Masumo et al.	09/15/1998	—
		5,904,550		Yamaguchi	05/18/1999	—
		5,773,309		Weiner	06/30/1998	—
		5,851,860		Makita et al.	12/22/1998	—
		5,707,882		Hamada et al.	01/13/1998	—
		5,365,875		Asai et al.	11/22/1994	—
		5,772,861		Meredith, Jr. et al.	06/30/1998	—
		5,747,201		Nakayama et al.	05/05/1998	—
		5,454,347		Shibata et al.	10/03/1995	—
		4,388,145		Hawkins et al.	06/14/1983	—
		5,529,630		Imahashi et al.	06/25/1996	—
		5,147,826		Liu et al.	09/15/1992	—
		5,275,851		Fonash et al.	01/04/1994	—
		5,569,610		Zhang et al.	10/29/1996	—
		4,332,833		Aspnes et al.	06/01/1982	—
		5,131,752		Yu et al.	07/21/1992	—
		5,387,309		Bobel et al.	02/07/1995	—
CL		5,472,515		Lee et al.	12/05/1995	—

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Office <sup>2</sup>	Number <sup>3</sup>	Kind Code <sup>2</sup> (if known)			
CL		JP	05-243576			09/21/1993	— Abst.
CL		JP	08-051078			02/20/1996	— Abst.
CL		JP	06-204132			07/22/1994	— Abst.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>3</sup>
CL		F. Ueno "Observation of fast microscopic phase change phenomena of chalcogenide thin films," Japanese Journal of Applied Physics, Supplement, Vol. 26, Supplement 26-4, pp. 55-60, 1987.	
CL		N. Kondo et al., "Film thickness measurement of ultrathin film using light of UV wavelength," Proceedings of the SPIE, Vol. 1673, pp. 392-402, 1992.	

Examiner Signature	<i>cahoul</i>	Date Considered	6.20.05
--------------------	---------------	-----------------	---------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

BEST AVAILABLE COPY

Please type a plus sign (+) inside this box → [+]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>			<b>Complete if Known</b>		
			Application Number	Based on SN 10/035,441	
			Filing Date	Filed: January 4, 2002	
			First Named Inventor	Naoaki YAMAGUCHI et al.	
			Group Art Unit	1765	
			Examiner Name	Anita Karen Alanko	
Sheet	2	of	3	Attorney Docket Number	0756-7191

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code <sup>2</sup> (if known)		
CL		5,503,707		Maung et al.	04/02/1996
		5,232,547		Drowley et al.	08/03/1993
		5,091,320		Aspnes et al.	02/25/1992
		5,494,697		Blayo et al.	02/27/1996
		5,456,763		Kaschmitter et al.	10/10/1995
		5,624,851		Takayama et al.	04/29/1997
		6,059,873		Yamaguchi et al.	05/09/2000
		6,054,739		Yamazaki et al.	04/25/2000
CL		4,469,551		Laude	09/04/1984

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Office <sup>2</sup>	Number <sup>2</sup>	Kind Code <sup>2</sup> (if known)		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>3</sup>
CL		C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon," (3 pages) Appl. Phys. Lett. 60(2) pp. 225-227, 1/1992.	
CL		A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," USSR, pp. 635-640, Phys. Stat. Sol. (A) Vol. 95, 1986.	
CL		T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films," Solid State Communications, Vol. 85, No. 11, pp. 921-924, 1993.	
CL		R. Kakkad, J. Smith, W.S. Lau, S.J. Fonash, "Crystallized Si Films by Low-Temperature Rapid Thermal Annealing of Amorphous Silicon," J. Appl. Phys. 65(5), March 1, 1989, 1989 American Institute of Physics, pp. 2069-2072	

Examiner Signature	<i>calomble</i>	Date Considered	6.30.05
--------------------	-----------------	-----------------	---------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

NOT AVAILABLE COPY